

Vishay Siliconix

P-Channel 30-V (D-S) MOSFET

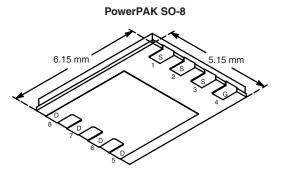
PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)			
- 30	0.0068 at V _{GS} = - 10 V	- 22			

FEATURES

- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFETs
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile

APPLICATIONS

- Battery and Load Switching
- Notebook Computers
- Notebook Battery Packs



Bottom View

Ordering Information: Si7459DP-T1-E3 (Lead (Pb)-free) Si7459DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise r	noted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 30		V	
Gate-Source Voltage		V _{GS}	± 25			
Continuous Drain Current /T 150°C\a	T _A = 25 °C	– I _D	- 22	- 13		
Continuous Drain Current $(T_J = 150^{\circ}C)^a$	T _A = 70 °C		- 17	- 10	А	
Pulsed Drain Current		I _{DM}	- 60		A	
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 4.5	- 1.6		
Maximum David Disairational	T _A = 25 °C	– P _D	5.4	1.9	W	
Maximum Power Dissipation ^a	T _A = 70 °C		3.4	1.2		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{b,c}			260		U	

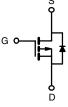
THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum lungtion to Ambienta	t ≤ 10 s	R _{thJA}	18	23	
Maximum Junction-to-Ambient ^a	Steady State		52	65	°C/W
Maximum Junction-to-Case (Drain)	Steady State		1.0	1.5	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



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Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{\rm DS} = V_{\rm GS}, I_{\rm D} = -250 \ \mu {\rm A}$			- 3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		± 100	~ ^		
		$V_{DS} = 0 V, V_{GS} = \pm 25 V$			± 200	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		- 1			
		V_{DS} = - 30 V, V_{GS} = 0 V, T_{J} = 70 °C	- 1			μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -10 V$	- 30			Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 22 A		0.0056	0.0068	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 22 A		50		S	
Diode Forward Voltage ^a	V _{SD}	$I_{S} = -2.9 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.71	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Qg			113	170	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = - 15 V, V_{GS} = - 10 V, I_D = - 22 A		17			
Gate-Drain Charge	Q _{gd}			32.5			
Turn-On Delay Time	t _{d(on)}			25	40	- ns	
Rise Time	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = - \ 15 \ V, \ R_{\text{L}} = 15 \ \Omega \\ I_{\text{D}} \cong - \ 1 \ A, \ V_{\text{GEN}} = - \ 10 \ V, \ R_{\text{g}} = 6 \ \Omega \end{array}$		20	30		
Turn-Off Delay Time	t _{d(off)}			180	270		
Fall Time	t _f			130	200		
Gate Resistance	R _g			4		Ω	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.9 A, dl/dt = 100 A/μs		100	150	ns	

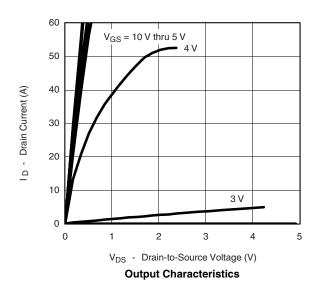
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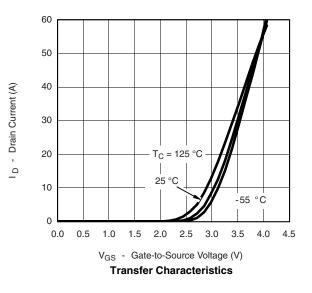
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

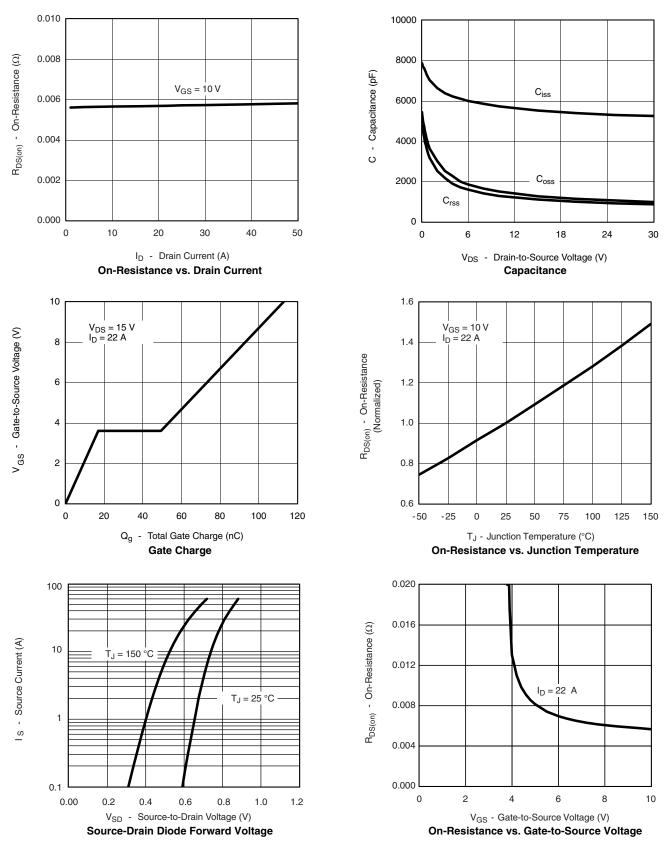
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







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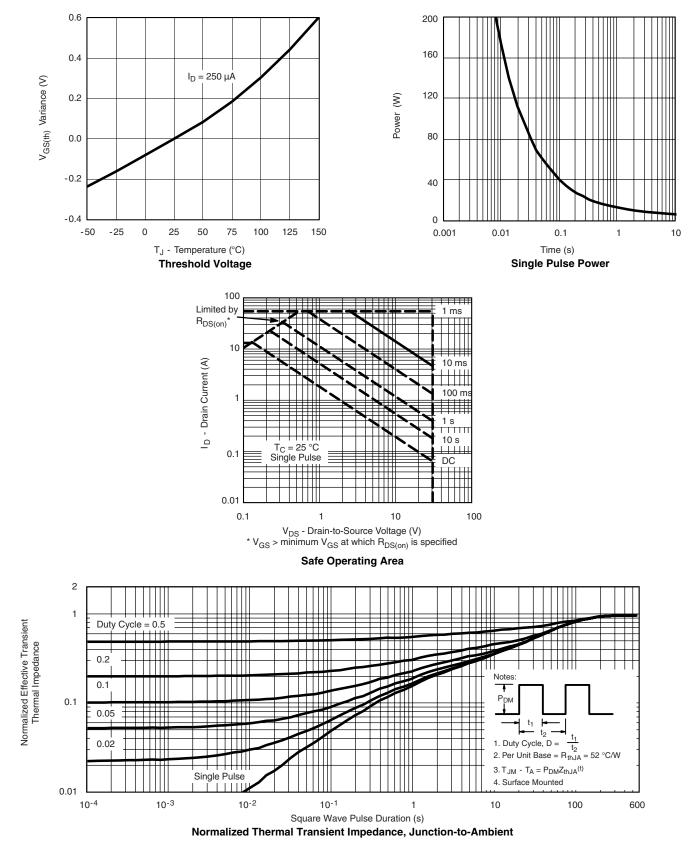


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Si7459DP

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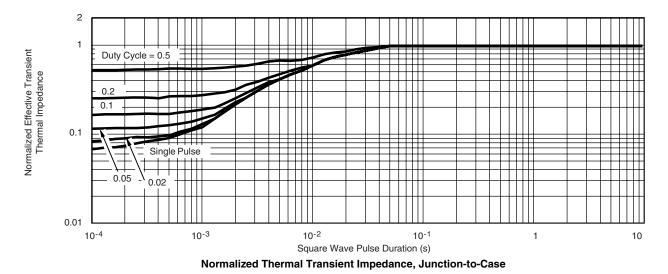








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Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72631.



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